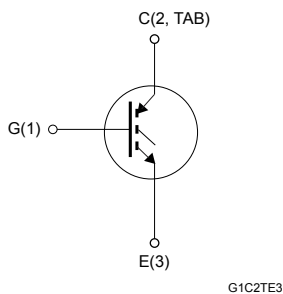
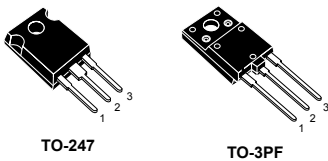


## Trench gate field-stop 650 V, 30 A high speed HB series IGBT



### Features

- Maximum junction temperature:  $T_J = 175\text{ }^\circ\text{C}$
- High speed switching series
- Minimized tail current
- $V_{CE(sat)} = 1.55\text{ V (typ.)}$  at  $I_C = 30\text{ A}$
- Tight parameters distribution
- Safe paralleling
- Low thermal resistance

### Applications

- Photovoltaic inverters
- Power factor correction
- Welding
- High-frequency converters

### Description

These devices are IGBTs developed using an advanced proprietary trench gate field-stop structure. These devices are part of the new HB series of IGBTs, which represent an optimum compromise between conduction and switching loss to maximize the efficiency of any frequency converter. Furthermore, the slightly positive  $V_{CE(sat)}$  temperature coefficient and very tight parameter distribution result in safer paralleling operation.

#### Product status links

[STGFW30H65FB](#)
[STGW30H65FB](#)

# 1 Electrical ratings

**Table 1. Absolute maximum ratings**

Symbol	Parameter	Value		Unit
		TO-247	TO-3PF	
$V_{CES}$	Collector-emitter voltage ( $V_{GE} = 0\text{ V}$ )	650		V
$I_C$	Continuous collector current at $T_C = 25\text{ °C}$	60		A
	Continuous collector current at $T_C = 100\text{ °C}$	30		A
$I_{CP}^{(1)}$	Pulsed collector current	120		A
$V_{GE}$	Gate-emitter voltage	±20		V
$P_{TOT}$	Total power dissipation at $T_C = 25\text{ °C}$	260	92	W
$V_{ISO}$	Insulation withstand voltage (RMS) from all three leads to external heat sink ( $t = 1\text{ s}$ ; $T_C = 25\text{ °C}$ )		3.5	kV
$T_{stg}$	Storage temperature range	-55 to 150		°C
$T_J$	Operating junction temperature range	-55 to 175		°C

1. Pulse width is limited by maximum junction temperature.

**Table 2. Thermal data**

Symbol	Parameter	Value		Unit
		TO-247	TO-3PF	
$R_{thJC}$	Thermal resistance, junction-to-case	0.58	1.63	°C/W
$R_{thJA}$	Thermal resistance, junction-to-ambient	50		°C/W

## 2 Electrical characteristics

$T_J = 25\text{ °C}$  unless otherwise specified

**Table 3. Static characteristics**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)CES}$	Collector-emitter breakdown voltage	$V_{GE} = 0\text{ V}, I_C = 2\text{ mA}$	650			V
$V_{CE(sat)}$	Collector-emitter saturation voltage	$V_{GE} = 15\text{ V}, I_C = 30\text{ A}$		1.55	2	V
		$V_{GE} = 15\text{ V}, I_C = 30\text{ A}, T_J = 125\text{ °C}$		1.65		
		$V_{GE} = 15\text{ V}, I_C = 30\text{ A}, T_J = 175\text{ °C}$		1.75		
$V_{GE(th)}$	Gate threshold voltage	$V_{CE} = V_{GE}, I_C = 1\text{ mA}$	5	6	7	V
$I_{CES}$	Collector cut-off current	$V_{GE} = 0\text{ V}, V_{CE} = 650\text{ V}$			25	$\mu\text{A}$
$I_{GES}$	Gate-emitter leakage current	$V_{CE} = 0\text{ V}, V_{GE} = \pm 20\text{ V}$			250	nA

**Table 4. Dynamic characteristics**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$C_{ies}$	Input capacitance	$V_{CE} = 25\text{ V}, f = 1\text{ MHz}, V_{GE} = 0\text{ V}$	-	3659	-	pF
$C_{oes}$	Output capacitance		-	101	-	pF
$C_{res}$	Reverse transfer capacitance		-	76	-	pF
$Q_g$	Total gate charge	$V_{CC} = 520\text{ V}, I_C = 30\text{ A}, V_{GE} = 0\text{ to }15\text{ V}$ (see Figure 27. Gate charge test circuit)	-	149	-	nC
$Q_{ge}$	Gate-emitter charge		-	25	-	nC
$Q_{gc}$	Gate-collector charge		-	62	-	nC

**Table 5. Switching characteristics (inductive load)**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{CE} = 400\text{ V}$ , $I_C = 30\text{ A}$ , $R_G = 10\ \Omega$ , $V_{GE} = 15\text{ V}$ (see Figure 26. Test circuit for inductive load switching)	-	37	-	ns
$t_r$	Current rise time		-	14.6	-	ns
$(di/dt)_{on}$	Turn-on current slope		-	1643	-	A/ $\mu$ s
$t_{d(off)}$	Turn-off delay time		-	146	-	ns
$t_f$	Current fall time		-	23	-	ns
$E_{on}^{(1)}$	Turn-on switching energy		-	151	-	$\mu$ J
$E_{off}^{(2)}$	Turn-off switching energy		-	293	-	$\mu$ J
$E_{ts}$	Total switching energy		-	444	-	$\mu$ J
$t_{d(on)}$	Turn-on delay time		$V_{CE} = 400\text{ V}$ , $I_C = 30\text{ A}$ , $R_G = 10\ \Omega$ , $V_{GE} = 15\text{ V}$ , $T_J = 175\text{ }^\circ\text{C}$ (see Figure 26. Test circuit for inductive load switching)	-	35	-
$t_r$	Current rise time	-		16.1	-	ns
$(di/dt)_{on}$	Turn-on current slope	-		1496	-	A/ $\mu$ s
$t_{d(off)}$	Turn-off-delay time	-		158	-	ns
$t_f$	Current fall time	-		65	-	ns
$E_{on}^{(1)}$	Turn-on switching energy	-		175	-	$\mu$ J
$E_{off}^{(2)}$	Turn-off switching energy	-		572	-	$\mu$ J
$E_{ts}$	Total switching energy	-		747	-	$\mu$ J

1. Including the reverse recovery of the external SiC diode STPSC206W.

2. Including the tail of the collector current.

## 2.1 Electrical characteristics (curves)

Figure 1. Output characteristics ( $T_J = 25^\circ\text{C}$ )

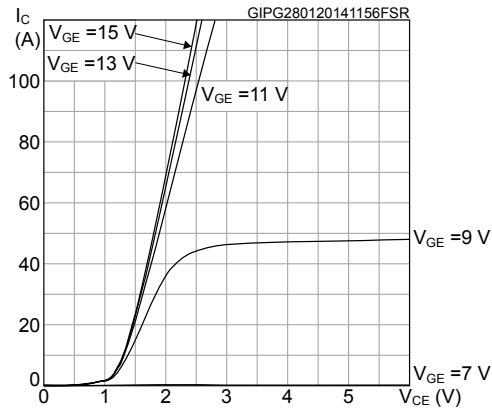


Figure 2. Output characteristics ( $T_J = 175^\circ\text{C}$ )

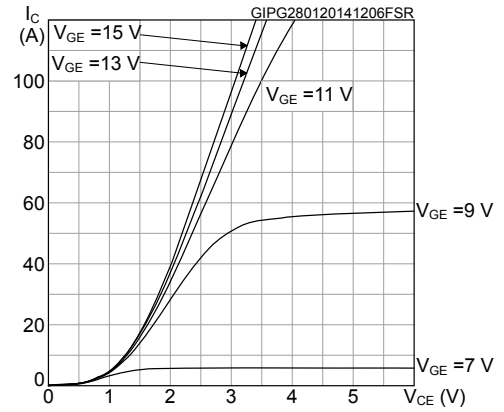


Figure 3. Transfer characteristics

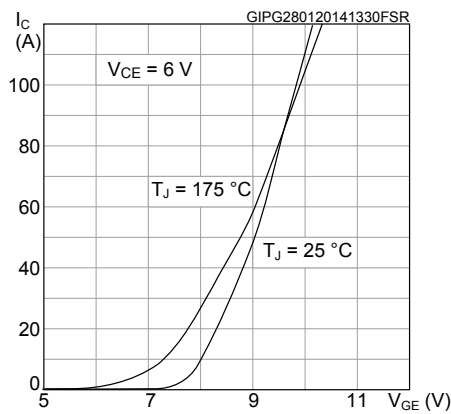


Figure 4. Collector current vs case temperature for TO-247

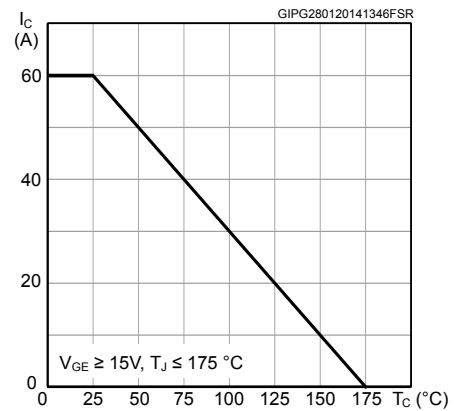


Figure 5. Collector current vs case temperature for TO-3PF

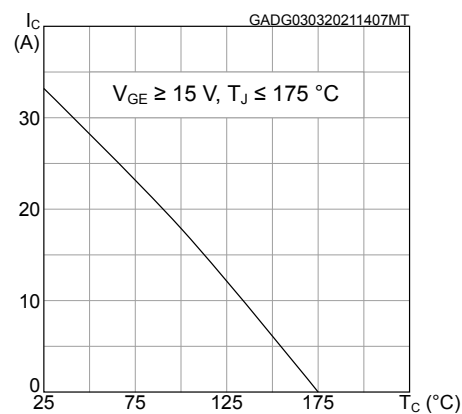
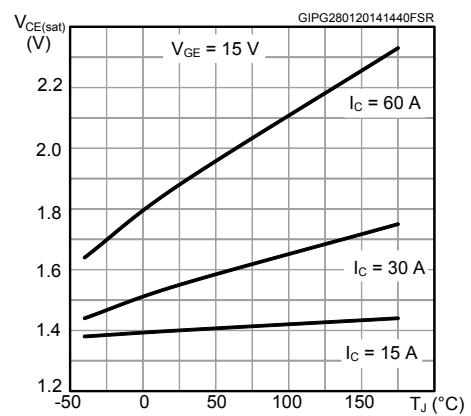
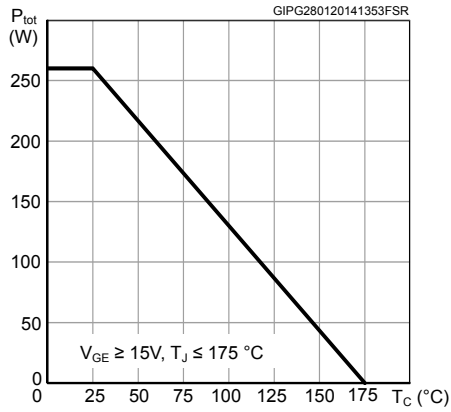
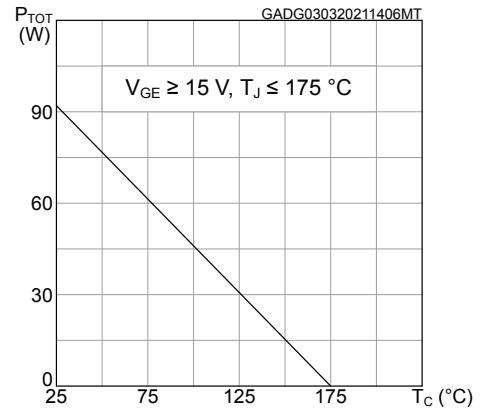
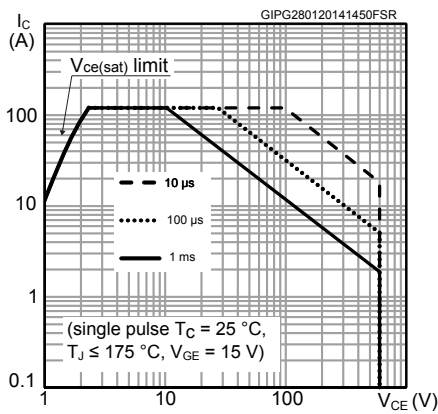
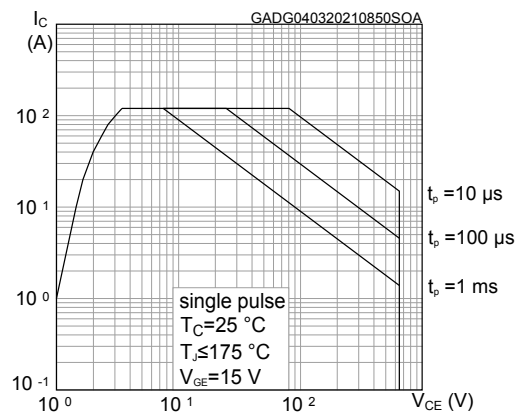
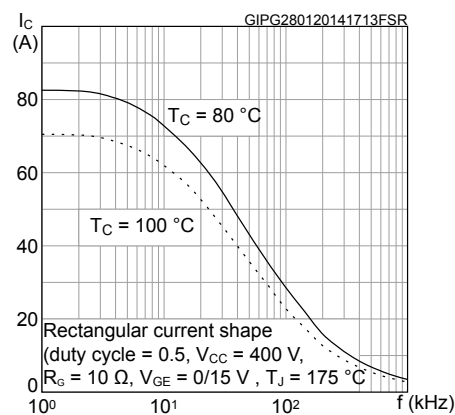
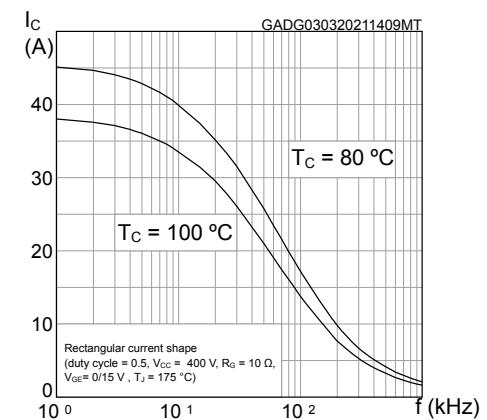
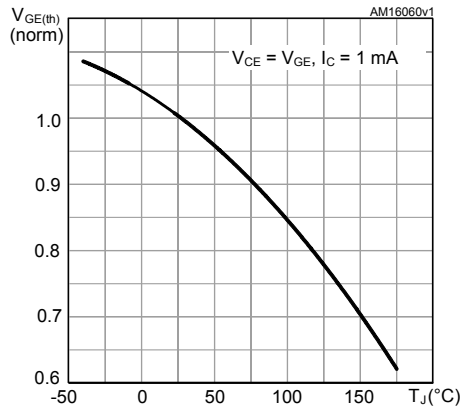
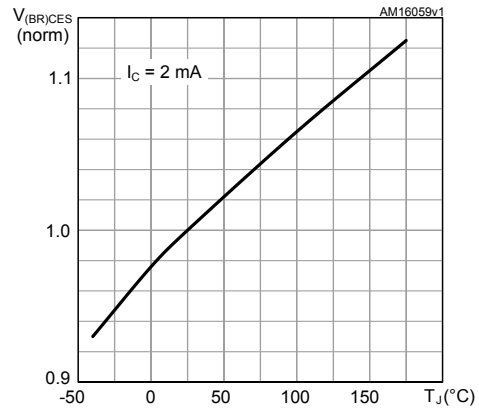
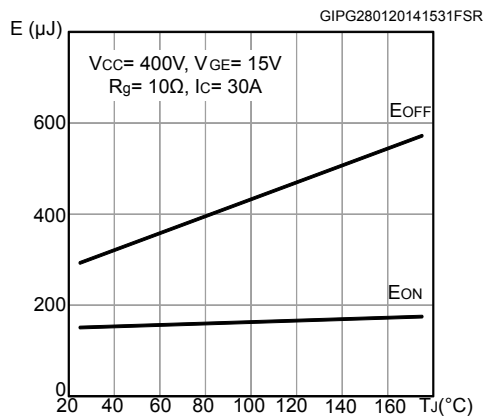
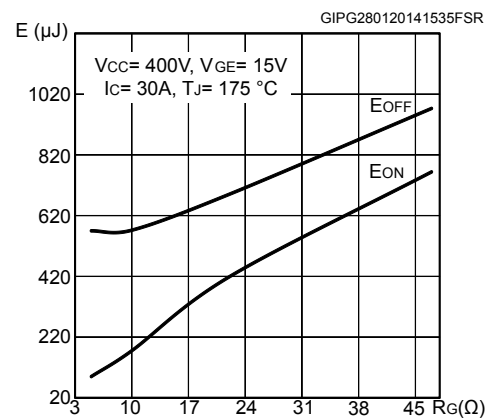
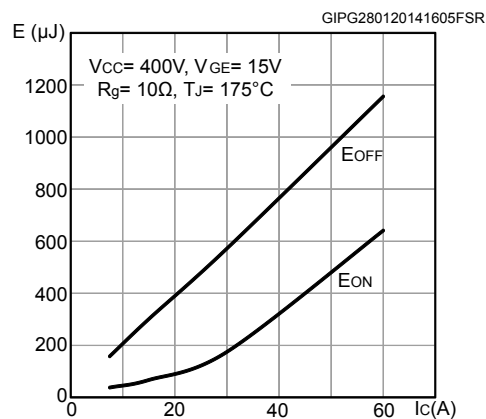
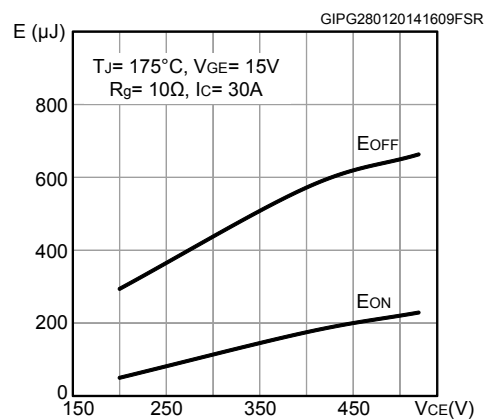
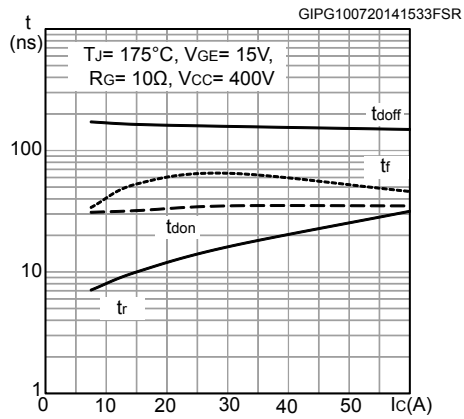
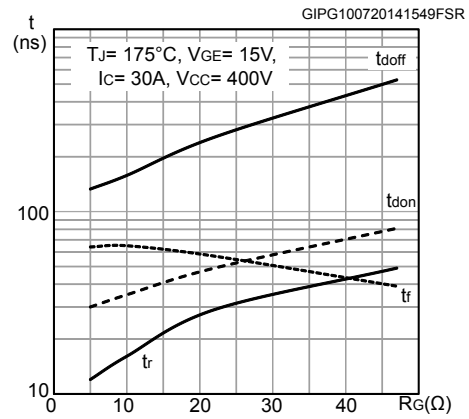
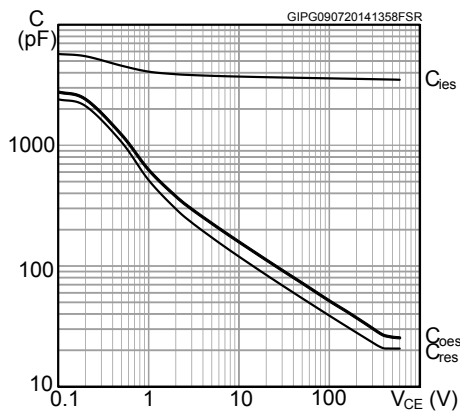
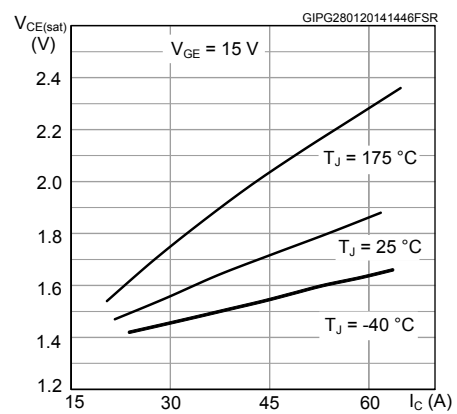
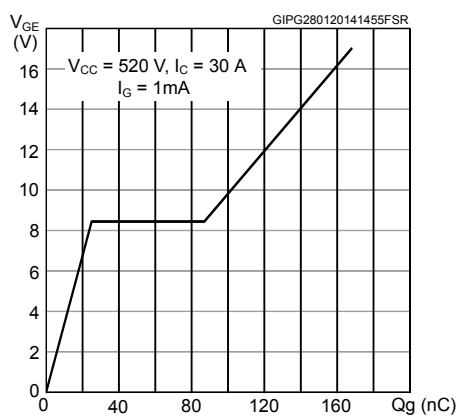
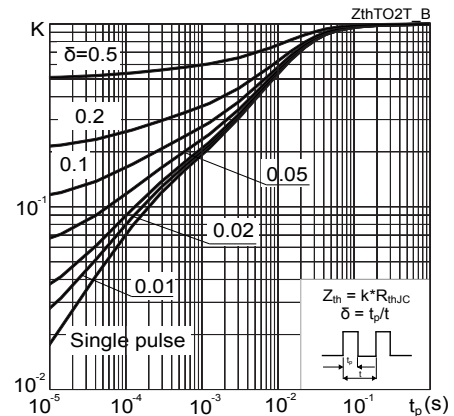


Figure 6.  $V_{CE(sat)}$  vs junction temperature

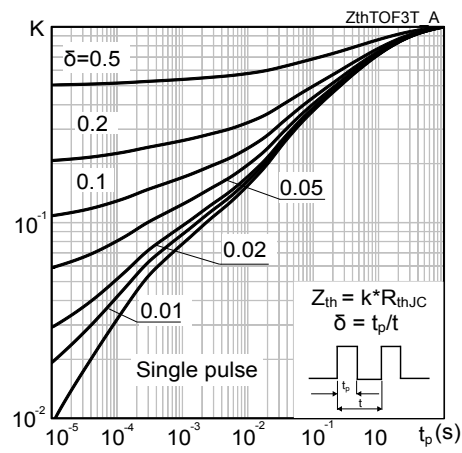


**Figure 7. Power dissipation vs case temperature for TO-247**

**Figure 8. Power dissipation vs case temperature for TO-3PF**

**Figure 9. Forward bias safe operating area for TO-247**

**Figure 10. Forward bias safe operating area for TO-3PF**

**Figure 11. Collector current vs switching frequency for TO-247**

**Figure 12. Collector current vs switching frequency for TO-3PF**


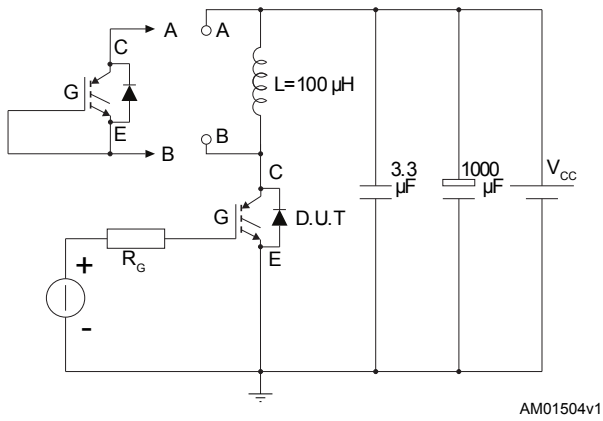
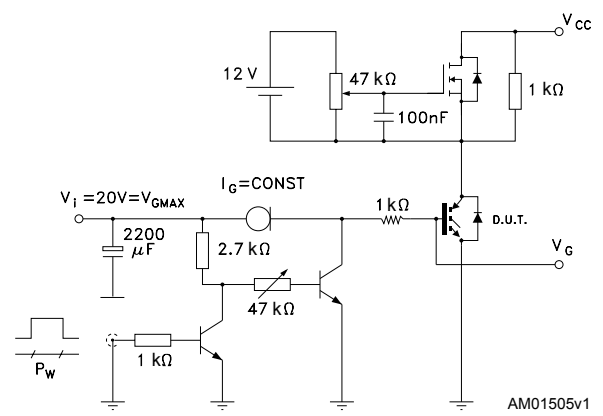
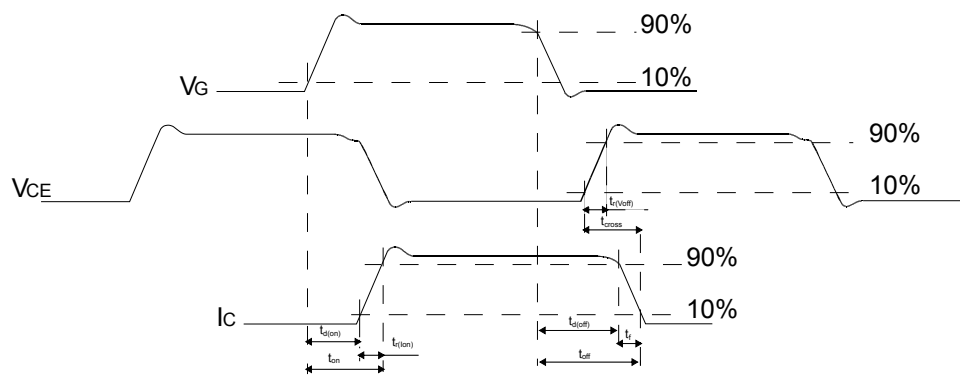
**Figure 13. Normalized  $V_{GE(th)}$  vs junction temperature**

**Figure 14. Normalized  $V_{(BR)CES}$  vs junction temperature**

**Figure 15. Switching energy vs temperature**

**Figure 16. Switching energy vs gate resistance**

**Figure 17. Switching energy vs collector current**

**Figure 18. Switching energy vs collector emitter voltage**


**Figure 19. Switching times vs collector current**

**Figure 20. Switching times vs gate resistance**

**Figure 21. Capacitance variations**

**Figure 22.  $V_{CE(sat)}$  vs collector current**

**Figure 23. Gate charge vs gate-emitter voltage**

**Figure 24. Thermal impedance for TO-247**




**Figure 25. Thermal impedance for in TO-3PF**


### 3 Test circuits

**Figure 26. Test circuit for inductive load switching**

**Figure 27. Gate charge test circuit**

**Figure 28. Switching waveform**


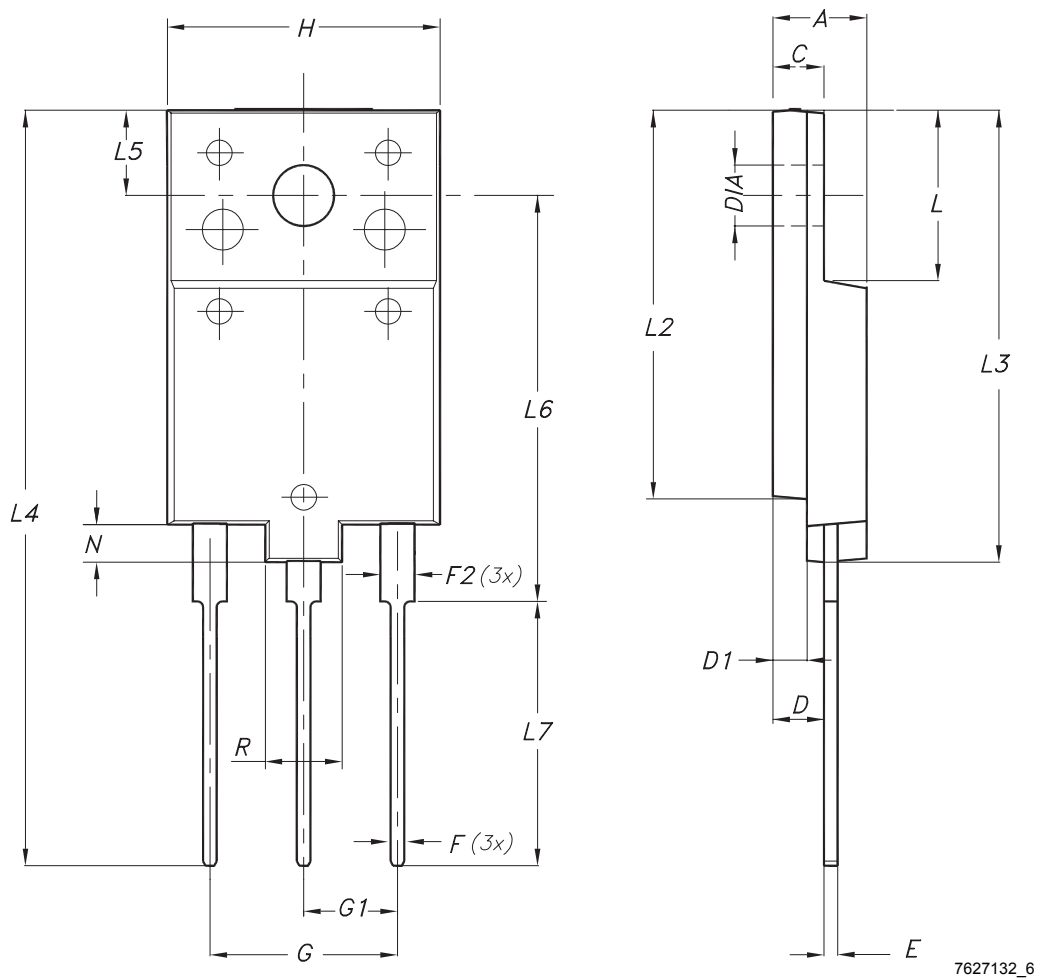
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## 4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of **ECOPACK** packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK is an ST trademark.

### 4.1 TO-3PF package information

Figure 29. TO-3PF package outline



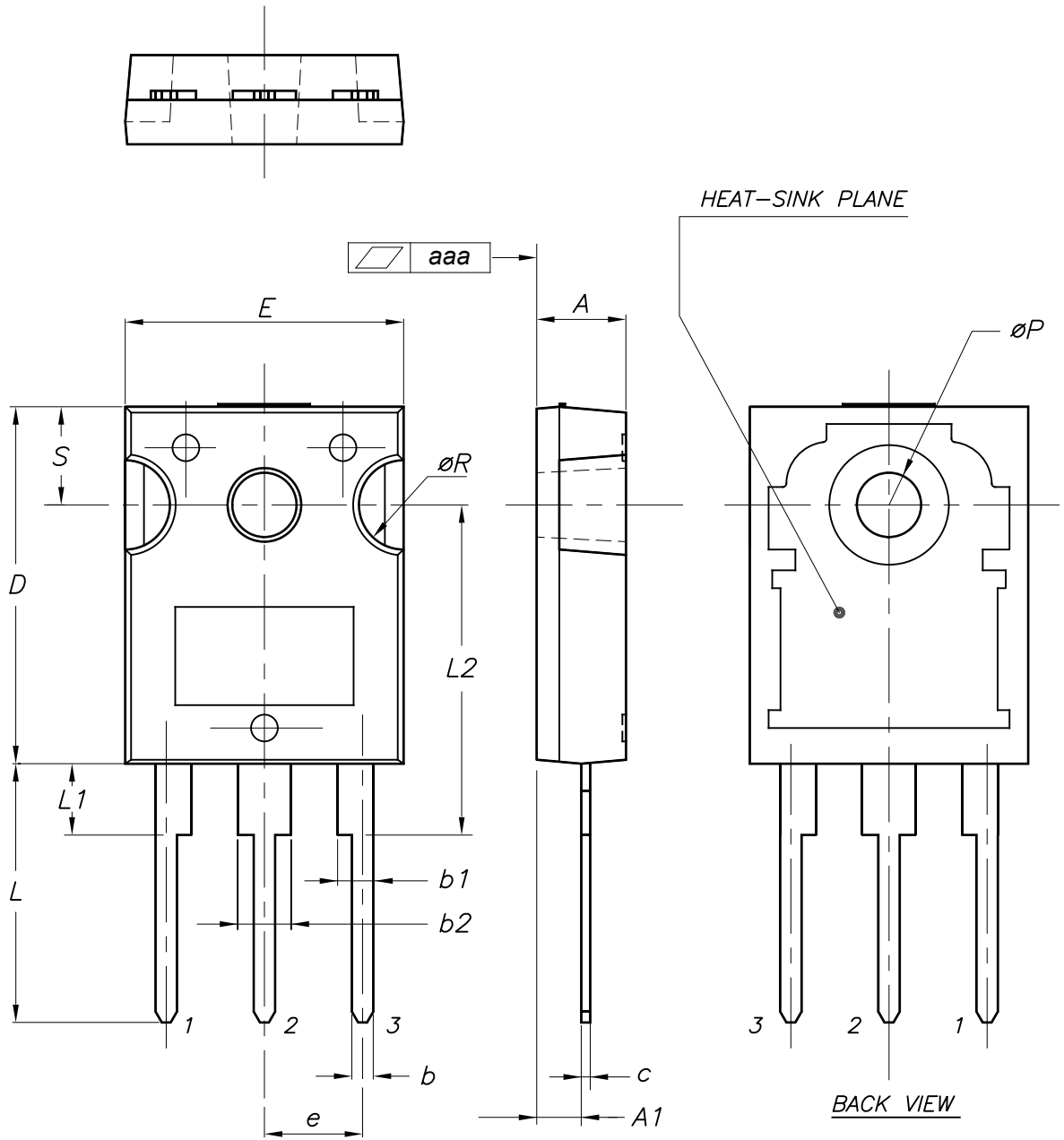
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Table 6. TO-3PF mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	5.30		5.70
C	2.80		3.20
D	3.10		3.50
D1	1.80		2.20
E	0.80		1.10
F	0.65		0.95
F2	1.80		2.20
G	10.30		11.50
G1		5.45	
H	15.30		15.70
L	9.80	10.00	10.20
L2	22.80		23.20
L3	26.30		26.70
L4	43.20		44.40
L5	4.30		4.70
L6	24.30		24.70
L7	14.60		15.00
N	1.80		2.20
R	3.80		4.20
Dia	3.40		3.80

## 4.2 TO-247 package information

Figure 30. TO-247 package outline



0075325\_10

**Table 7. TO-247 package mechanical data**

Dim.	mm		
	Min.	Typ.	Max.
A	4.85		5.15
A1	2.20		2.60
b	1.0		1.40
b1	2.0		2.40
b2	3.0		3.40
c	0.40		0.80
D	19.85		20.15
E	15.45		15.75
e	5.30	5.45	5.60
L	14.20		14.80
L1	3.70		4.30
L2		18.50	
ØP	3.55		3.65
ØR	4.50		5.50
S	5.30	5.50	5.70
aaa		0.04	0.10

## 5 Ordering information

**Table 8. Order codes**

Order code	Marking	Package	Packing
STGFW30H65FB	G30H65FB	TO-3PF	Tube
STGW30H65FB	GW30H65FB	TO-247	

## Revision history

**Table 9. Document revision history**

Date	Revision	Changes
28-Jan-2014	1	Initial release.
24-Feb-2014	2	Updated units in <i>Table 6: Switching characteristics (inductive load)</i> for Ets, and updated note 1. Update <i>Figure 16: Switching losses vs temperature</i> , <i>Figure 17: Switching losses vs gate resistance</i> and <i>Figure 18: Switching losses vs collector current</i> . Updated title and features in cover page. Minor text changes.
10-Mar-2014	3	Added device in TO-3PF. Updated <i>Table 1: Device summary</i> , <i>Table 2: Absolute maximum ratings</i> , <i>Table 3: Thermal data</i> . Added <i>Figure 6: Collector current vs. case temperature for TO-3PF</i> , <i>Figure 9: Power dissipation vs. case temperature for TO-3PF</i> , <i>Figure 11: Forward bias safe operating area for TO-3PF</i> and <i>Figure 26: Thermal impedance for TO-3PF</i> . Updated <i>Section 4: Package information</i> .
20-May-2014	4	Updated <i>Table 2: Absolute maximum ratings</i> .
28-Jul-2015	5	Text and formatting changes throughout document Updated <i>Table 2: Absolute maximum ratings</i> Updated <i>Section 2.1: Electrical characteristics (curves)</i> Updated <i>Section 3: Test circuits</i> Updated <i>Section 4.2: TO-247 package information</i> Updated <i>Section 4.3: TO-3P package information</i>
27-Apr-2020	6	Updated applications in cover page. Updated <i>Table 8. Order codes</i> . Minor text changes.
16-Mar-2021	7	The part number STGWT30H65FB has been removed and the document has been updated accordingly. Updated <a href="#">Section 1 Electrical ratings</a> and <a href="#">Section 2.1 Electrical characteristics (curves)</a> . Minor text changes.



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